

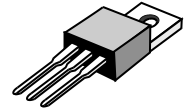
## Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

- \* Low Forward Voltag.
- \* Low Switching noise.
- \* High Current Capacity
- \* Guarantee Reverse Avalance.
- \* Guard-Ring for Stress Protection.
- \* Low Power Loss & High efficiency.
- \* 125°C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Cnduction.
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

### SCHOTTKY BARRIER RECTIFIERS

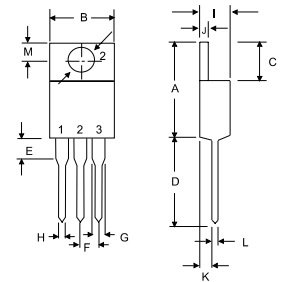
**10 AMPERES  
70 – 100 VOLTS**



**TO-220AB**

### MAXIMUM RATINGS

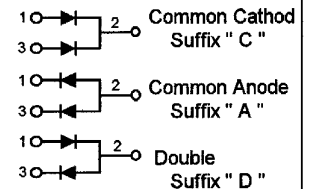
Characteristic	Symbol	S10C				Unit
		70	80	90	100	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	70	80	90	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	56	63	70	V
Average Rectifier Forward Current Total Device (Rated $V_R$ , $T_c=100^\circ\text{C}$ )	$I_{F(AV)}$	5.0 10				A
Peak Repetitive Forward Current (Rate $V_R$ , Square Wave, 20kHz)	$I_{FM}$	10				A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	$I_{FSM}$	125				A
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	- 65 to + 125				°C



DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.32
B	9.78	10.42
C	6.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	2.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.36
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

### ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	S10C				Unit
		70	80	90	100	
Maximum Instantaneous Forward Voltage ( $I_F=5.0$ Amp, $T_c = 25^\circ\text{C}$ ) ( $I_F=5.0$ Amp, $T_c = 100^\circ\text{C}$ )	$V_F$	0.75 0.67		0.85 0.76		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_c = 25^\circ\text{C}$ ) (Rated DC Voltage, $T_c = 125^\circ\text{C}$ )	$I_R$	1.0 30				mA



# S10C70 , S10C80

FIG-1 FORWARD CURRENT DERATING CURVE

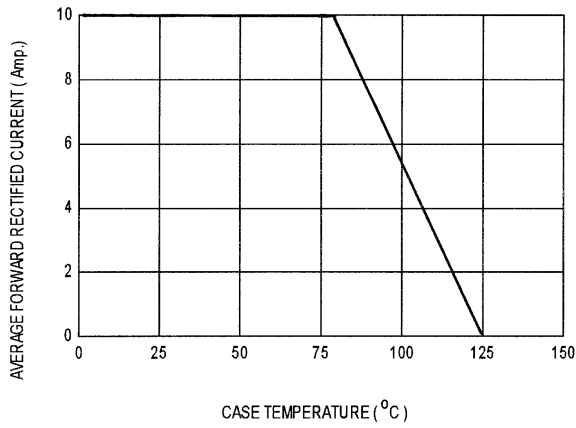


FIG-2 TYPICAL FORWARD CHARACTERISTICS

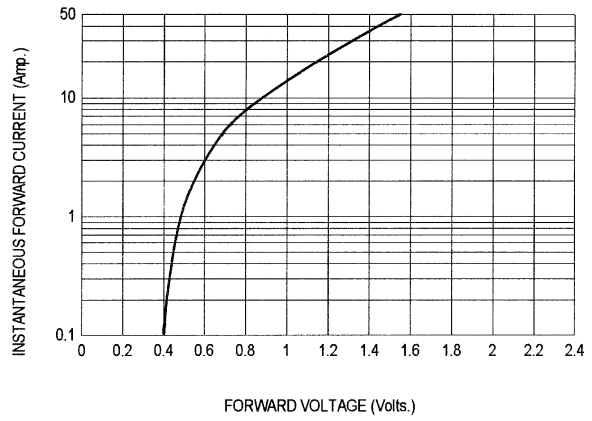


FIG-3 TYPICAL REVERSE CHARACTERISTICS

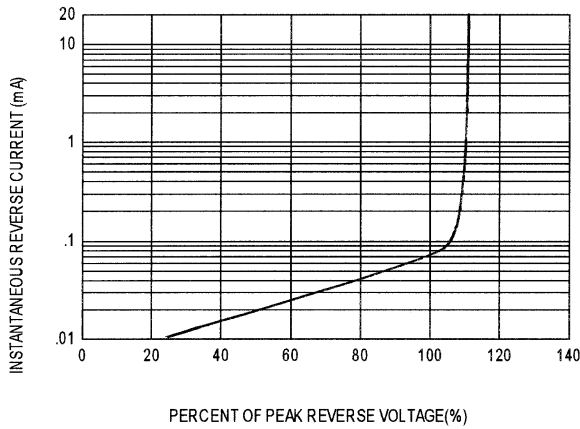


FIG-4 TYPICAL JUNCTION CAPACITANCE

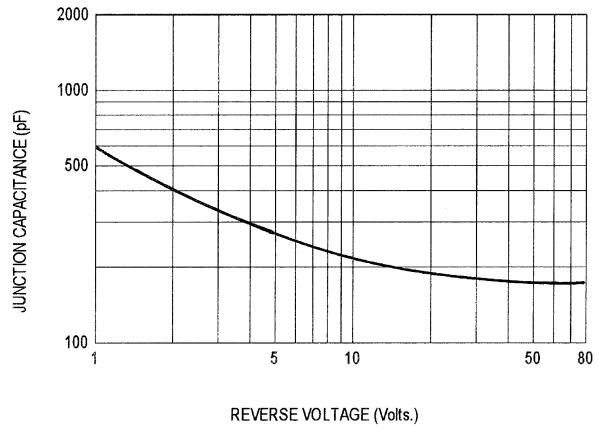
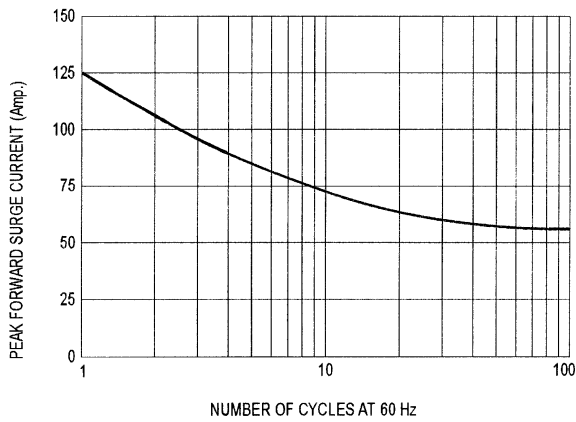


FIG-5 PEAK FORWARD SURGE CURRENT



# S10C90, S10C100

FIG-1 FORWARD CURRENT DERATING CURVE

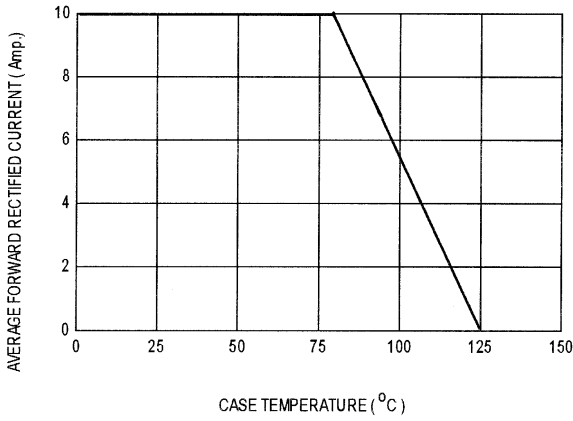


FIG-2 TYPICAL FORWARD CHARACTERISTICS

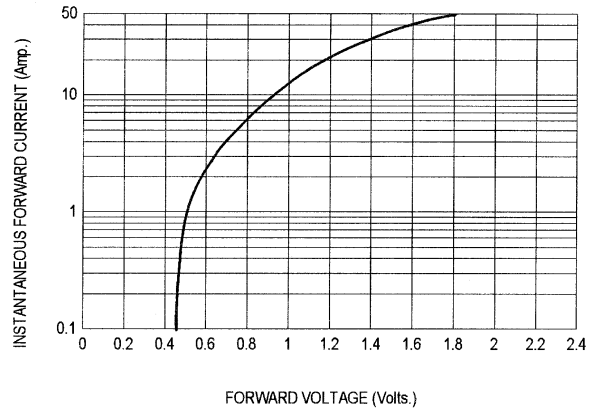


FIG-3 TYPICAL REVERSE CHARACTERISTICS

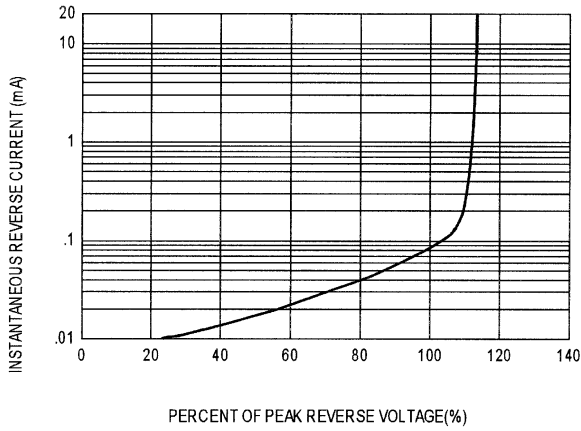


FIG-4 TYPICAL JUNCTION CAPACITANCE

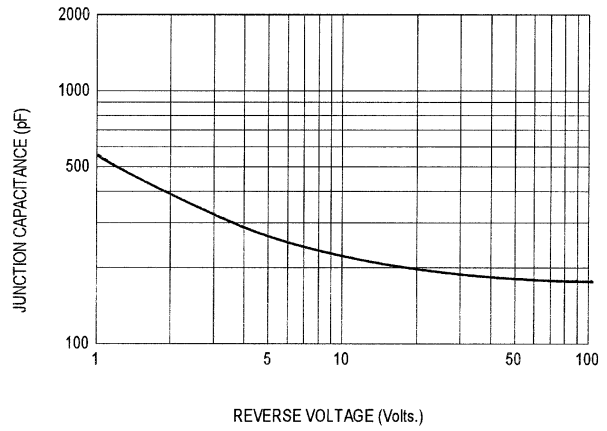


FIG-5 PEAK FORWARD SURGE CURRENT

